

Subp1  
cont  
~~hook-shaped hard mask being a polysilicon film, tungsten film,  
or other electroconductive film, or a silicon nitride film or  
other insulating film.~~

AddA2  
~~5. The manufacturing method of a semiconductor IC device  
described in Claim 1 or 4, characterized by the fact that the  
aforementioned connecting holes are in contact with the lower  
electrodes in the capacitors of the memory cells, with the  
capacitors being set for storing information on the bit lines.~~

INS13  
~~ABSTRACT~~

865020-28061050  
~~To provide a manufacturing method of the semiconductor IC  
device having fine-structure connecting holes or trenches with  
high dimensional precision. There is the following step of the  
operation: a hook-shaped hard mask made of polysilicon film 18  
and polysilicon film 20a is formed on the surface of silica film  
17 for forming connecting holes 21 accommodating plugs that  
perform an electrical connection with the lower portion of the  
lower~~

